Notice of Allowability	Application No.	Applicant(s)
	10/053,572	OHNUMA, HIDETO
	Examiner	Art Unit
	Scott Geyer	2812
The MAILING DATE of this communication appears on the cover sheet with the correspondence address— All claims being allowable, PROSECUTION ON THE MERITS IS (OR REMAINS) CLOSED in this application. If not included herewith (or previously mailed), a Notice of Allowance (PTOL-85) or other appropriate communication will be mailed in due course. THIS NOTICE OF ALLOWABILITY IS NOT A GRANT OF PATENT RIGHTS. This application is subject to withdrawal from issue at the initiative of the Office or upon petition by the applicant. See 37 CFR 1.313 and MPEP 1308.  1.  This communication is responsive to		
2. The allowed claim(s) is/are 1-20 and 22-39.		
<ul> <li>2.</li></ul>		
Attachment(s)  1. Notice of References Cited (PTO-892)  2. Notice of Draftperson's Patent Drawing Review (PTO-948)  3. Information Disclosure Statements (PTO-1449 or PTO/SB/O Paper No./Mail Date  4. Examiner's Comment Regarding Requirement for Deposit of Biological Material	6. Interview Summary Paper No./Mail Da 08), 7. Examiner's Amende	te

## **DETAILED ACTION**

## Election/Restrictions

Applicant's election without traverse of claims 1, 3, 4, 6, 7, 9, 10, 12, 13, 15, 16, 18, 19, 20, 23, 26, 27, 28, 30, 31, 33, 34, 36 and 38 in the reply filed on May 5<sup>th</sup>, 2006 is acknowledged.

However, due to the establishment of allowable subject matter in the independent claims, the restriction requirement presented in the office action dated April 3, 2006 is hereby withdrawn. Claims 1-20 and 22-39 are treated on their merits below.

## Allowable Subject Matter

Claims 1-20 and 22-39 are allowed.

The following is an examiner's statement of reasons for allowance.

The prior art of record and to the examiner's knowledge does not teach or render obvious, at least to the skilled artisan, the instant invention regarding:

A method of making a semiconductor device comprising formation of a silicon semiconductor film and crystallization of the silicon film, particularly characterized by forming a chemical oxide on a surface of the crystallized silicon film with a liquid chemical, and doping the crystallized silicon film, as recited in independent claims 1, 23 and 28.

A method of making a semiconductor device comprising formation of a silicon semiconductor film and crystallization of the silicon film, particularly characterized by terminating dangling bonds on a surface of the crystallized silicon film with oxygen and doping the crystallized silicon film as recited in independent claims 2 and 29.

A method of making a semiconductor device comprising formation of a silicon semiconductor film and crystallization of the silicon film, particularly characterized by terminating dangling bonds on a surface of the crystallized silicon film with an element to be bonded with a bonding energy higher than that of Si-H bonds, and doping the crystallized silicon film as recited in independent claims 3 and 30.

Any comments considered necessary by applicant must be submitted no later than the payment of the issue fee and, to avoid processing delays, should preferably accompany the issue fee. Such submissions should be clearly labeled "Comments on Statement of Reasons for Allowance."

## Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Scott Geyer whose telephone number is (571) 272-1958. The examiner can normally be reached on weekdays, between 10:00am - 6:30pm. If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Michael Lebentritt can be reached on (571) 272-1873. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300. Information regarding the status of an application may be obtained from

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the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free). If you would like assistance from a USPTO Customer Service Representative or access to the automated information system, call 800-786-9199 (IN USA OR CANADA) or 571-272-1000.

> SCOTT B. GEYER PRIMARY EXAMINER

SBG August 5, 2006 ND-7 8/5/06